

AMENDMENTS TO THE CLAIMS

Please amend claims 1-5, 10, 20-22, and 24 as shown below. The claims have been amended to insure uniformity between the claims and the specification. Please cancel claim 27.

1 1. (Currently Amended) A semiconductor package comprising:
2 a package support member ~~substrate~~;
3 a plurality of pins attached to said package support member ~~substrate~~;
4 a plurality of package leads in electrical communication with said plurality of
5 pins; and
6 a stand-alone radiation power source mounted to said semiconductor package.

1 2. (Currently Amended) The semiconductor package of claim 1, further
2 comprising an IC mounted to said package support member ~~substrate~~ and in electrical
3 communication with said plurality of package leads.

1 3. (Currently Amended) The semiconductor package of claim 1, wherein
2 said stand-alone radiation power source is mounted on said package support member
3 ~~substrate~~.

1 4. (Currently Amended) The semiconductor package of claim 1, further
2 comprising a top package member coupled to said package support member ~~substrate~~,
3 wherein said stand-alone radiation power source is mounted to said top package member.

1 5. (Currently Amended) The semiconductor package of claim 1, further
2 comprising a top package member coupled to said package support member ~~substrate~~,
3 wherein said stand-alone radiation power source is contained within said top package
4 member.

1 6. (Original) The semiconductor package of claim 1, wherein said
2 semiconductor package is selected from the group consisting of DIPs, PQFPs, SIPs, ceramic
3 flatpacks, PIN packages, SOIC packages, QSOPs, LCC packages, and PLCCs.

1 7. (Original) The semiconductor package of claim 2, wherein said IC is a
2 MEMs device.

1 8. (Original) The semiconductor package of claim 2, wherein said stand-
2 alone radiation power source is electrically coupled to said IC via a pair of package substrate
3 leads.

1 9. (Original) The semiconductor package of claim 1, further comprising
2 at least a pair of power source leads in electrical communication with at least a pair of
3 corresponding IC package leads.

1 10. (Currently Amended) The semiconductor package of claim 1, further
2 comprising at least a pair of power source leads in electrical communication with at least a
3 pair of said plurality of pins attached to said package support member ~~substrate~~.

1 11. (Original) The semiconductor package of claim 1, wherein said stand-
2 alone radiation power source is a beta cell.

1 12. (Original) The semiconductor package of claim 11, wherein said beta
2 cell is comprised of an icosahedral boride semiconductor.

1 13. (Original) The semiconductor package of claim 1, wherein said stand-
2 alone radiation power source is comprised of a homo-junction.

1 14. (Original) The semiconductor package of claim 1, wherein said stand-
2 alone radiation power source is comprised of a hetero-junction.

1 15. (Original) The semiconductor package of claim 1, wherein said stand-
2 alone radiation power source is mounted to said semiconductor package via eutectics.

1 16. (Original) The semiconductor package of claim 1, wherein said stand-
2 alone radiation power source is mounted to said semiconductor package via epoxies.

1 17. (Original) The semiconductor package of claim 1, wherein said stand-
2 alone radiation power source is mounted to said semiconductor package via glass frit
3 materials.

1 18. (Original) The semiconductor package of claim 1, further comprising
2 radiation shielding.

1 19. (Original) The semiconductor package of claim 18, wherein said
2 radiation shielding at least partially encompasses said stand-alone radiation power source.

1 20. (Currently Amended) The semiconductor package of claim 4, wherein
2 said top package member is hermetically sealed to said package support member ~~substrate~~.

1 21. (Currently Amended) The semiconductor package of claim 5, wherein
2 said top package member is hermetically sealed to said package support member ~~substrate~~.

1 22. (Currently Amended) The semiconductor package of claim 1, wherein
2 said package support member ~~substrate~~ is fabricated from a ceramic, a plastic or a PCB.

1 23. (Original) The semiconductor package of claim 1, wherein said stand-
2 alone radiation power source is connected to a portion of said plurality of package leads via
3 wire interconnects.

1 24. (Currently Amended) A semiconductor package comprising:
2 a package support member ~~substrate~~;
3 an IC die support member mounted to said package support member;
4 an IC mounted to said IC die support member ~~package-substrate~~, said IC
5 having a plurality of contact pads;
6 a plurality of package leads on said package support member ~~substrate~~;
7 a plurality of wire interconnects in electrical communication with said
8 plurality of contact pads and said plurality of package leads;
9 a plurality of pins in electrical communication with said plurality of package
10 leads;

11 a package lid attached to said package support member substrate; and
12 a stand-alone radiation power source mounted to said package lid.

1 25. (Original) The semiconductor package of claim 24, wherein said
2 stand-alone radiation power source is electrically coupled to at least a pair of said plurality of
3 contact pads.

1 26. (Original) The semiconductor package of claim 24, wherein said
2 stand-alone radiation power source is electrically coupled to at least a pair of said plurality of
3 pins.

1 27. (Canceled)

1 28. (Original) The semiconductor package of claim 24, wherein said
2 semiconductor package is selected from the group consisting of DIPs, PQFPs, SIPs, ceramic
3 flatpacks, PIN packages, SOIC packages, QSOPs, LCC packages, and PLCCs.

1 29. (Original) The semiconductor package of claim 24, wherein said
2 stand-alone radiation power source is a beta cell.

1 30. (Original) The semiconductor package of claim 29, wherein said beta
2 cell is comprised of an icosahedral boride semiconductor.

1 31. (Original) The semiconductor package of claim 24, wherein said
2 stand-alone radiation power source is comprised of a homo-junction.

1 32. (Original) The semiconductor package of claim 24, wherein said
2 stand-alone radiation power source is comprised of a hetero-junction.